

1 Scope

The present specifications shall apply to Sanken silicon diode, FMC-26UA.

2 Outline

Type	Silicon Rectifier Diode	
Structure	Resin Molded	Flammability: UL94V-0 (Equivalent)
Applications	High Frequency Rectification, etc.	

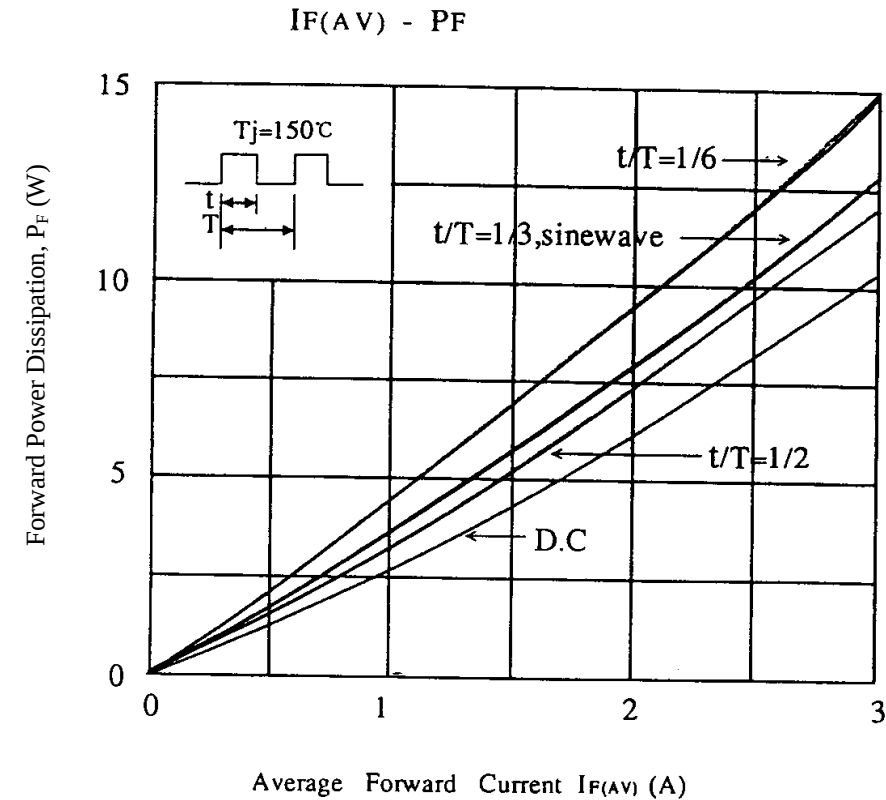
3 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	1200	
2	Peak Reverse Voltage	V_{RM}	V	1200	
3	Average Forward Current	$I_{F(AV)}$	A	3.0	$T_c=98^{\circ}\text{C}$, sinewave
4	Peak Surge Forward Current	I_{FSM}	A	50	10ms Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	12.5	
6	Junction Temperature	T_j	$^{\circ}\text{C}$	-40 to +150	
7	Storage Temperature	T_{stg}	$^{\circ}\text{C}$	-40 to +150	
8	Screwing Torque		$\text{N}\cdot\text{m}$	0.59	
9	Dielectric Strength		kV	A.C. 1.0	Junction and case (1min.)

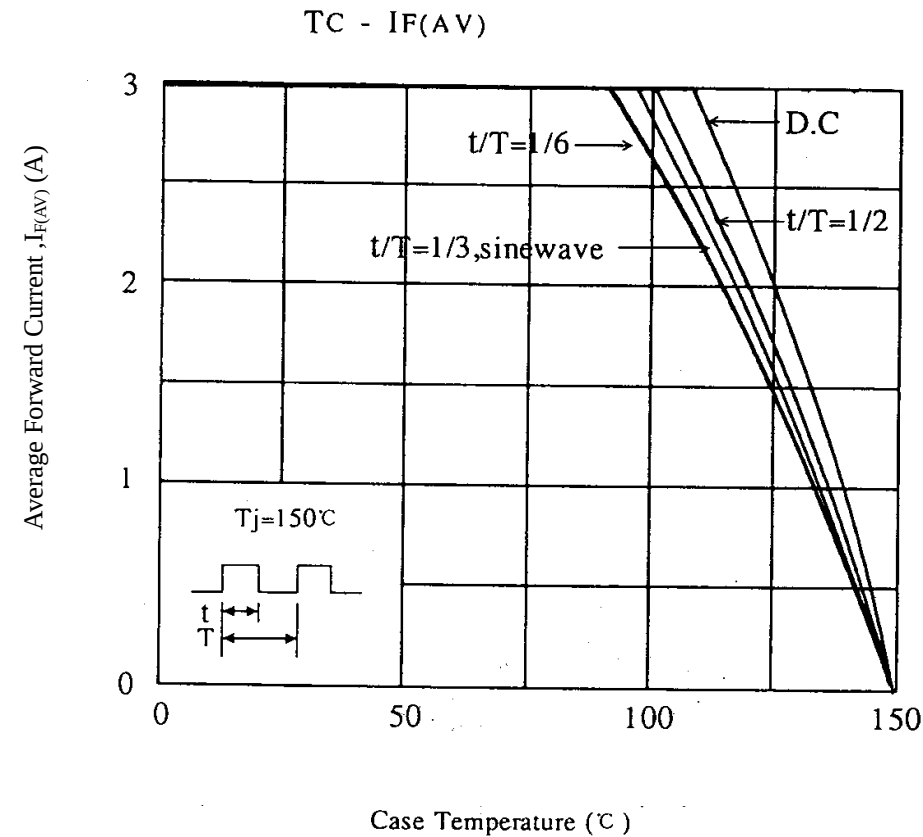
4 Electrical characteristics ($T_a=25^{\circ}\text{C}$, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	V_F	V	4.0 max.	$I_F=3.0\text{A}$
2	Reverse Leakage Current	I_R	μA	500 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	mA	3 max.	$V_R=V_{RM}$, $T_j=150^{\circ}\text{C}$
4	Reverse Recovery Time	trr1	ns	70 max.	$I_F=I_{RP}=500\text{mA}$ 90% Recovery point, $T_j=25^{\circ}\text{C}$
		trr2	ns	35 max.	$I_F=0.5\text{A}$, $I_{RP}=1\text{A}$ 75% Recovery point, $T_j=25^{\circ}\text{C}$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}\text{C}/\text{W}$	4.0 max.	Between Junction and case

5 Characteristics

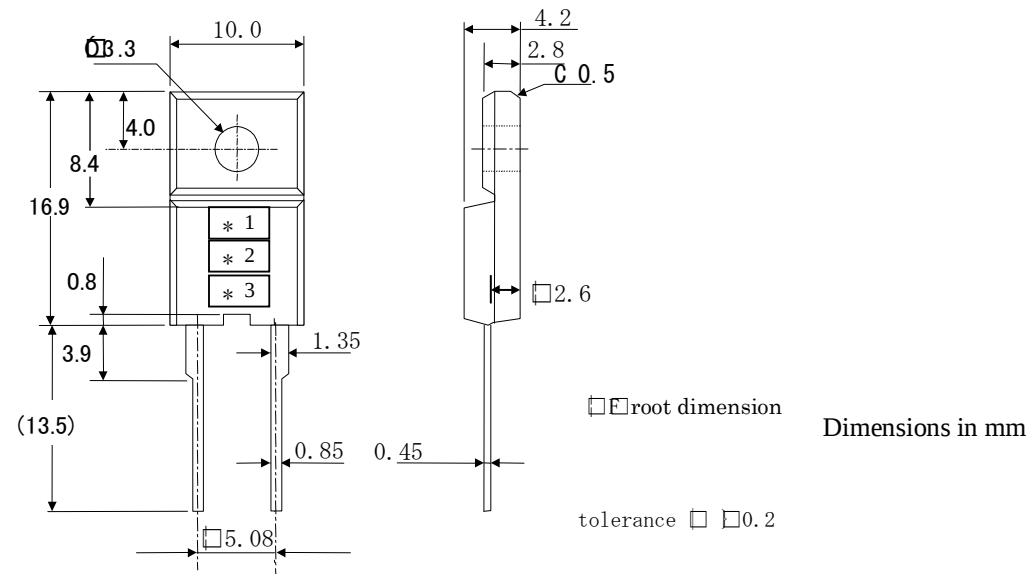


6 Derating



7 Package information

7-1 Package type, physical dimensions and material



7-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

7-3 Marking

Type Name	Marking		
	*1 is type name	*2 is polarity	*3 is lot number
FMC-26UA	FMC26U		1st letter: Last digit of year 2nd letter: Month From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 4N11 (Nov. 11, 2004)